Semiconductor Growth, Surfaces and Interfaces

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Contents

	Contributors	vii
	Preface	xi
1	Surface reconstruction of GaAs (001) during OMCVD growth I. Kamiga, D.E. Aspnes, H. Tanaka, L.T. Florez, M.A. Koza, R. Bhat and J.P. Harbison	1
2	Optical in situ surface control during MOVPE and MBE growth Wolfgang Richter	11
3	Lateral quantum size effects created by growth induced surface and interface corregations on non-(100)-oriented substrates Klaus H. Ploog and Richard Nötzel	27
4	Fabrication of quantum well wires and vertical quantum wells on submicron gratings by MOVPE G. Vermeire, F. Vermaerke, P. Van Daele and P. Demeester	39
5	Evolution of surface morphology during epitaxial growth D.D. Vredensky, N. Haider, T. Shitara and P. Šmilauer	51
6	Reaction Models for the Epitaxial growth of III–V semiconductors by chemical beam epitaxy J.S. Foord, C.L. French, C.L. Leroguer and G.J. Davies	65
7	The continuing drama of the semiconductor interface J.M. Woodall, P.D. Kirchner, J.L. Freeouf, D.T. McInturff, M.R. Melloch and F.H. Pollak	79
8	STM studies of Fermi-level pinning on the GaAS (001) surface M.D. Pashley	91
9	Probing semiconductor interfaces by transmission electron microscopy J.W. Steeds and D. Cherns	103
10	Monitoring growth with X-ray diffraction C. Norris	115
11	Electron states at semiconductor interfaces: the intrinsic and extrinsic charge neutrality levels F. Flores, R. Pérez, R. Rincón and R. Saiz Pardo	
12	Control of electrical barriers at semiconductor heterojunctions by interface doping C.C. Matthai	137
13	In situ characterization and control of compound semiconductor interfaces Hideki Hasegawa	145
	Index	155